

256Kx16 Static RAM
High Speed
CMOS, Module

ADVANCE INFORMATION

T-46-23-14

Features

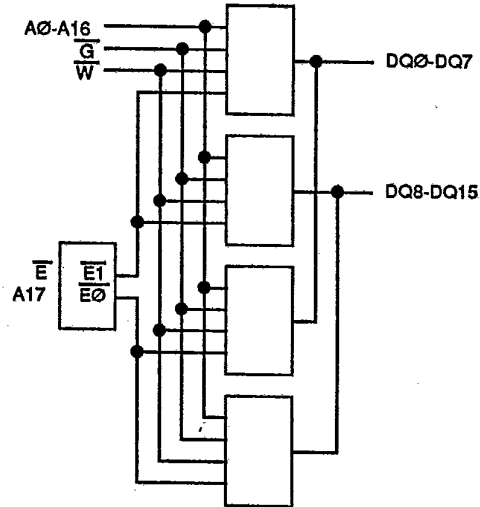
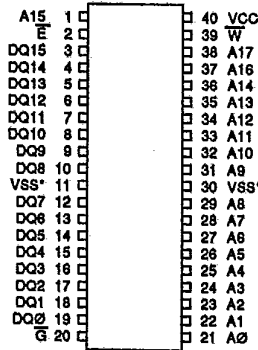
The EDI8M16257C is a 256Kx16 CMOS Static RAM Module consisting of four (4) 128Kx8 CMOS Static RAMs in leadless chip carriers surface mounted onto a multi-layered ceramic substrate. The 128Kx8 RAMs are organized as two banks of 128Kx16 bits each.

- 256Kx16 bit CMOS Static Random Access Memory Module
- Access Times 35, 45 and 55ns
 - Fully Static, No Clocks
 - Inputs and Outputs Directly TTL Compatible
- High Density Packaging
- 40 Pin DIP, No. 126
- Single +5V (±10%) Supply Operation

Fully asynchronous circuitry requires no clocks or refreshing for operation and provides equal access and cycle times for ease of use.

Military modules, incorporating semiconductor components which are compliant to MIL-STD-883, paragraph 1.2.1, are available.

Pin Configuration and Block Diagram



Pin Names

| | |
|----------|--------------------|
| A0-A17 | Address Inputs |
| E | Chip Enable |
| W | Write Enable |
| G | Output Enable |
| DQ0-DQ15 | Data Input/ Output |
| VCC | Power (+5V±10%) |
| VSS | Ground |
| NC | No Connection |

*Note: Both ground pins (VSS) need to be grounded for proper operation.